

# EAST SEARCH FOR 10-773,863

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	155	semiconductor adj (exhaust or waste or offgas)	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T
2	BRS	L2	145018	((high adj temperature) or hot) adj air	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T
3	BRS	L3	4	1 same 2	US- PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T

	Time Stamp	Comments	Error Definition	Errors
1	2006/11/20 08:49			
2	2006/11/20 08:50			
3	2006/11/20 08:50			

DERWENT- 2006-327021

ACC-NO:

DERWENT- 200634

WEEK:

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**TITLE:** Method for increasing purification efficiency of exhaust from a semiconductor production process comprises ejecting hot air at the exhaust outlet end in an exhaust treatment tank for directly fully purifying harmful material in the exhaust

**INVENTOR:** FENG, W

**PATENT-ASSIGNEE:** ORIENT SERVICE CO LTD[ORIEN]

**PRIORITY-DATA:** 2003TW-0103924 (February 25, 2003)

**PATENT-FAMILY:**

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
TW 230240 B1	April 1, 2005	N/A	000	F23G 007/06
TW 200416369 A	September 1, 2004	N/A	000	F23G 007/06

**APPLICATION-DATA:**

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
TW 230240B1	N/A	2003TW-0103924	February 25, 2003
TW 200416369A	N/A	2003TW-0103924	February 25, 2003

**INT-CL (IPC):** F23G007/06

**ABSTRACTED-PUB-NO:** TW 200416369A

**BASIC-ABSTRACT:**

NOVELTY - A method for increasing the purification efficiency of an exhaust from a semiconductor production process mainly comprises:

forcibly ejecting a hot air at the exhaust outlet end in an exhaust treatment tank for directly fully purifying harmful material in the exhaust by using the feature where the hot air has an optimal catalytic temperature at the outlet end, thereby increasing the purification efficiency of the semiconductor exhaust.

CHOSEN- Dwg.0/0

DRAWING:

TITLE- METHOD INCREASE PURIFICATION EFFICIENCY EXHAUST

TERMS: SEMICONDUCTOR PRODUCE PROCESS COMPRISE EJECT HOT AIR  
EXHAUST OUTLET END EXHAUST TREAT TANK PURIFICATION HARM  
MATERIAL EXHAUST

DERWENT-CLASS: Q73

SECONDARY-ACC-NO:

Non-CPI Secondary Accession Numbers: N2006-276818

DERWENT- 2006-654260

ACC-NO:

DERWENT- 200668

WEEK:

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TITLE: Method for cleaning harmful materials of semiconductor waste gas to accelerate chemical reaction of harmful materials included in semiconductor waste gas

INVENTOR: FENG, W N

PATENT-ASSIGNEE: FENG W N[FENGI]

PRIORITY-DATA: 2004KR-0009264 (February 12, 2004)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
KR 2005081035	A August 18, 2005	N/A	000	H01L 021/02

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
KR2005081035A	N/A	2004KR-0009264	February 12, 2004

INT-CL (IPC): H01L021/02

ABSTRACTED-PUB-NO: KR2005081035A

BASIC-ABSTRACT:

NOVELTY - A method for cleaning harmful materials of semiconductor waste gas is provided to accelerate a chemical reaction of harmful materials included in semiconductor waste gas by guiding high temperature air to an outlet of waste gas of a semiconductor gas reducing system.

DETAILED DESCRIPTION - Hot air(30) is injected into a waste gas outlet(13) of a semiconductor gas reducing system(1). The hot air is

sent to semiconductor waste gas(4) exhausted from the waste gas outlet to accelerate the reaction of harmful materials in the semiconductor waste gas. The hot air is generated from a hot air generating unit(2).(C) KIPO 2006Image 1/1

CHOSEN- Dwg.1/1  
DRAWING:

TITLE- METHOD CLEAN HARM MATERIAL SEMICONDUCTOR WASTE GAS  
TERMS: ACCELERATE CHEMICAL REACT HARM MATERIAL SEMICONDUCTOR  
WASTE GAS

DERWENT-CLASS: U11

EPI-CODES: U11-C15Q;